IN THE CLAIMS

A listing of all claims and their current status in accordance with 37 C.F.R. § 1.121(c) is provided below.

1-10. (Canceled).

11. (previously presented) The method of claim 21, wherein mechanically coupling the die stack comprises:

(a) picking up the first die having a topside and an underside with a die picking tool;

(b) applying the adhesive to the underside of the first die, thereby providing an adhesively coated underside of the first die; and

(c) without releasing the first die from the die picking tool, picking up a second die having a topside and an underside by placing the adhesively coated underside of the first die against the topside of the second die, thereby forming a die stack.

12. (original) The method, as set forth in claim 11, wherein the first die is thicker than the second die.

13. (original) The method, as set forth in claim 11, wherein the acts (a), (b), and (c) are performed in the recited order.

14. (original) The method, as set forth in claim 11, wherein act (b) is performed before act (a).

15. (original) The method, as set forth in claim 11, comprising the act of applying adhesive to the underside of the second die, thereby providing an adhesively coated underside of the second die.

16. (original) The method, as set forth in claim 15, comprising the act of without releasing the first die from the picking tool, picking up a third die having a topside and an underside by placing the adhesively coated underside of the second die against the topside of the third die.

17-20. (Canceled).

21. (previously presented) A method of forming a semiconductor package comprising the acts of:

forming a die stack before placing the die stack on a temporary holding surface, wherein the die stack comprises an adhesive on at least one surface of a first die, wherein forming the die stack comprises mechanically coupling the die stack together via the adhesive, and electrically coupling the die stack together via bond wires or conductive balls;

picking the die stack from the temporary holding surface; and

placing the die stack on a substrate.

22. (previously presented) The method, as set forth in claim 21, comprising the act of curing the die stack before the act of picking the die stack.

23. (previously presented) The method, as set forth in claim 21, comprising the act of testing the die stack before the act of picking the die stack.

24. (previously presented) The method, as set forth in claim 21, wherein the act of picking the die stack from a temporary holding surface comprises the act of picking the die stack from a tape reel.

25. (previously presented) The method, as set forth in claim 21, wherein the act of picking the die stack from a temporary holding surface comprises the act of picking the die stack from a gel pack.

26. (previously presented) The method, as set forth in claim 21, wherein the act of picking the die stack from a temporary holding surface comprises the act of picking the die stack from a tray.

27. (previously presented) The method, as set forth in claim 21, wherein the act of picking the die stack from a temporary holding surface comprises the act of picking the die stack from a wafer.

28. (previously presented) The method, as set forth in claim 21, wherein the die stack comprises at least two semiconductor die.

29. (previously presented) The method, as set forth in claim 21, wherein the die stack comprises at least three semiconductor die.

30. (previously presented) The method, as set forth in claim 21, wherein the die stack comprises at least two semiconductor die stacked in a shingled configuration.

31. (previously presented) The method, as set forth in claim 21, comprising the acts of:

applying the adhesive between each die in the die stack, the adhesive being curable at a first temperature; and

applying a second adhesive between the die stack and the substrate, the second adhesive being curable at a second temperature lower than the first temperature.

32. (previously presented) The method, as set forth in claim 21, comprising the act of using the die stack on the substrate to form an integrated circuit package.

33. (previously presented) The method, as set forth in claim 32, comprising the act of electrically coupling the integrated circuit package to a processor to form an electronic system.

34. (previously presented) The method, as set forth in claim 21, wherein at least one die in the die stack comprises a memory die.